

## AMENDMENTS TO THE CLAIMS

1. **(Currently Amended)** A thin film-forming sputtering target material having high reflectance, ~~characterized by being~~said material being composed of an Ag base alloy containing 0.0058-1.0 mass% of P.
2. **(Currently Amended)** A thin film-forming sputtering target material having high reflectance, ~~characterized by being~~said material being composed of an Ag base alloy containing 0.0058-1.0 mass% of P and 0.01-2.0 mass% of at least one metallic element selected from In, Sn and Zn.
3. **(Currently Amended)** A thin film-forming sputtering target material having high reflectance, ~~characterized by being~~said material being composed of an Ag base alloy containing 0.0058-1.0 mass% of P, 0.01-0.9 mass% of Au and/or 0.001-5.0 mass% of Pd and/or 0.01-0.9 mass% of Pt.
4. **(Currently Amended)** A thin film-forming sputtering target material having high reflectance, ~~characterized by being~~said material being composed of an Ag base alloy containing 0.0058-1.0 mass% of P and 0.01-5.0 mass% of at least one metallic element selected from Cu, Ni, Fe and Bi.
5. **(Currently Amended)** A thin film-forming sputtering target material having high reflectance, ~~characterized by being~~said material being composed of an Ag base alloy containing 0.0058-1.0 mass% of P, 0.01-2.0 mass% of at least one metallic element selected from In, Sn and Zn, 0.01 to 0.9 mass% of Au and /or 0.01-5.0 mass% of Pd and/or 0.01-0.9 mass% of Pt.

**6. (Currently Amended)** A thin film-forming sputtering target material having high reflectance, ~~characterized by beingsaid material being~~ composed of an Ag base alloy containing 0.0058-1.0 mass% of P, 0.01-2.0 mass% of at least one metallic element selected from In, Sn and Zn, and 0.01-5.0 mass% of at least one metallic element selected from Cu, Ni, Fe and Bi.

**7. (Currently Amended)** A thin film-forming sputtering target material having high reflectance, ~~characterized by beingsaid material being~~ composed of an Ag base alloy containing 0.0058-1.0 mass% of P, 0.01-0.9 mass% of Au and/or 0.01-5.0 mass% of Pd and/or 0.01-0.9 mass% of Pt, and 0.01-5.0 mass% of at least one metallic element selected from Cu, Ni, and Bi.

**8. (Currently Amended)** A thin film-forming sputtering target material having high reflectance, ~~characterized by beingsaid material being~~ composed of an Ag base alloy containing 0.0058-1.0 mass% of P, 0.01-2.0 mass% of at least one metallic element selected from In, Sn and Zn, 0.01-0.9 mass% of Au and/or 0.01-5.0 mass% of Pd and/or 0.01-0.9 mass% of Pt, and 0.01-5.0 mass% of at least one metallic element selected from Cu, Ni, Fe and Bi.

**9. (Previously Presented)** Thin film formed of an Ag base alloy as set forth in Claim 1.

**10. (Previously Presented)** Thin film formed of an Ag base alloy as set forth in Claim 2.

**11. (Previously Presented)** Thin film formed of an Ag base alloy as set forth in Claim 3.

**12. (Previously Presented)** Thin film formed of an Ag base alloy as set forth in Claim 4.

**13. (Previously Presented)** Thin film formed of an Ag base alloy as set forth in Claim 5.

**14. (Previously Presented)** Thin film formed of an Ag base alloy as set forth in Claim 6.

**15. (Previously Presented)** Thin film formed of an Ag base alloy as set forth in Claim 7.

**16. (Previously Presented)** Thin film formed of an Ag base alloy as set forth in Claim 8.